

ABSTRACT OF DISCLOSURE

A solid image capturing element comprising a plurality of vertical shift registers arranged to each correspond to a column 5 of a plurality of light receiving pixels in a matrix arrangement, a horizontal shift register provided on an output side of the plurality of vertical shift registers, and an output section provided on an output side of the horizontal shift register. In this solid image capturing element, a reverse conductive 10 semiconductor region is formed over one major surface of one conductive semiconductor substrate, the plurality of light receiving pixels, the plurality of vertical shift registers, the horizontal shift register, and the output section are formed in the semiconductor region, and a portion of the semiconductor region 15 where the output section is formed has a higher dopant concentration than the portion of the semiconductor region where the horizontal shift register is formed.